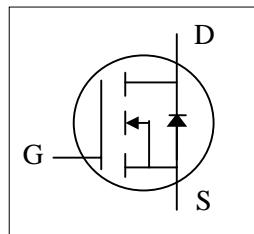
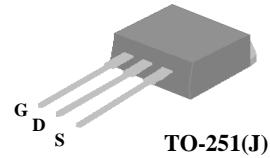
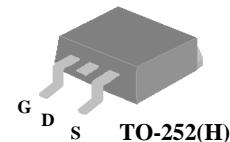




- ▼ Simple Drive Requirement
- ▼ Lower On-resistance
- ▼ Fast Switching Characteristic
- ▼ Halogen Free & RoHS Compliant



BV_{DSS}	60V
$R_{DS(ON)}$	36mΩ
I_D	22A



Description

AP9971A series are from Advanced Power innovative design and silicon process technology to achieve the lowest possible on-resistance and fast switching performance. It provides the designer with an extreme efficient device for use in a wide range of power applications.

The TO-252 package is widely preferred for all commercial-industrial surface mount applications using infrared reflow technique and suited for high current application due to the low connection resistance. The through-hole version (AP9971AGJ) are available for low-profile applications.

Absolute Maximum Ratings@ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Rating	Units
V_{DS}	Drain-Source Voltage	60	V
V_{GS}	Gate-Source Voltage	+20	V
$I_D @ T_C = 25^\circ\text{C}$	Drain Current, $V_{GS} @ 10\text{V}$	22	A
$I_D @ T_C = 100^\circ\text{C}$	Drain Current, $V_{GS} @ 10\text{V}$	14	A
I_{DM}	Pulsed Drain Current ¹	80	A
$P_D @ T_C = 25^\circ\text{C}$	Total Power Dissipation	34.7	W
T_{STG}	Storage Temperature Range	-55 to 150	°C
T_J	Operating Junction Temperature Range	-55 to 150	°C

Thermal Data

Symbol	Parameter	Value	Units
R_{thj-c}	Maximum Thermal Resistance, Junction-case	3.6	°C/W
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient (PCB mount) ³	62.5	°C/W
R_{thj-a}	Maximum Thermal Resistance, Junction-ambient	110	°C/W



AP9971AGH/J-HF

Electrical Characteristics @ $T_j=25^\circ\text{C}$ (unless otherwise specified)

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
BV_{DSS}	Drain-Source Breakdown Voltage	$V_{\text{GS}}=0\text{V}, I_{\text{D}}=1\text{mA}$	60	-	-	V
$R_{\text{DS}(\text{ON})}$	Static Drain-Source On-Resistance ²	$V_{\text{GS}}=10\text{V}, I_{\text{D}}=15\text{A}$	-	-	36	$\text{m}\Omega$
		$V_{\text{GS}}=6\text{V}, I_{\text{D}}=10\text{A}$	-	-	50	$\text{m}\Omega$
$V_{\text{GS}(\text{th})}$	Gate Threshold Voltage	$V_{\text{DS}}=V_{\text{GS}}, I_{\text{D}}=250\text{\mu A}$	1	-	3	V
g_{fs}	Forward Transconductance	$V_{\text{DS}}=10\text{V}, I_{\text{D}}=15\text{A}$	-	12.4	-	S
I_{DSS}	Drain-Source Leakage Current	$V_{\text{DS}}=60\text{V}, V_{\text{GS}}=0\text{V}$	-	-	10	\mu A
I_{GSS}	Gate-Source Leakage	$V_{\text{GS}}= \pm 20\text{V}, V_{\text{DS}}=0\text{V}$	-	-	± 100	nA
Q_g	Total Gate Charge	$I_{\text{D}}=15\text{A}$	-	17	27	nC
Q_{gs}	Gate-Source Charge	$V_{\text{DS}}=48\text{V}$	-	2.5	-	nC
Q_{gd}	Gate-Drain ("Miller") Charge	$V_{\text{GS}}=10\text{V}$	-	6.4	-	nC
$t_{\text{d}(\text{on})}$	Turn-on Delay Time	$V_{\text{DS}}=30\text{V}$	-	6.6	-	ns
t_r	Rise Time	$I_{\text{D}}=15\text{A}$	-	22	-	ns
$t_{\text{d}(\text{off})}$	Turn-off Delay Time	$R_{\text{G}}=3.3\Omega$	-	17	-	ns
t_f	Fall Time	$V_{\text{GS}}=10\text{V}$	-	4.3	-	ns
C_{iss}	Input Capacitance	$V_{\text{GS}}=0\text{V}$	-	625	1000	pF
C_{oss}	Output Capacitance	$V_{\text{DS}}=25\text{V}$	-	90	-	pF
C_{rss}	Reverse Transfer Capacitance	$f=1.0\text{MHz}$	-	65	-	pF

Source-Drain Diode

Symbol	Parameter	Test Conditions	Min.	Typ.	Max.	Units
V_{SD}	Forward On Voltage ²	$I_{\text{S}}=15\text{A}, V_{\text{GS}}=0\text{V}$	-	-	1.3	V
t_{rr}	Reverse Recovery Time	$I_{\text{S}}=15\text{A}, V_{\text{GS}}=0\text{V}$	-	27	-	ns
Q_{rr}	Reverse Recovery Charge	$dI/dt=100\text{A}/\mu\text{s}$	-	26	-	nC

Notes:

1. Pulse width limited by Max. junction temperature.
2. Pulse test
3. Surface mounted on 1 in² copper pad of FR4 board

THIS PRODUCT IS SENSITIVE TO ELECTROSTATIC DISCHARGE, PLEASE HANDLE WITH CAUTION.

USE OF THIS PRODUCT AS A CRITICAL COMPONENT IN LIFE SUPPORT OR OTHER SIMILAR SYSTEMS IS NOT AUTHORIZED.

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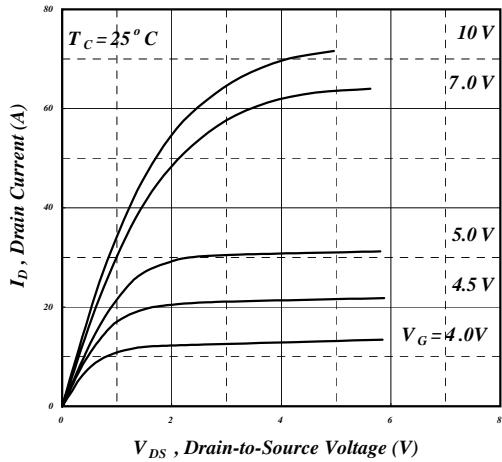


Fig 1. Typical Output Characteristics

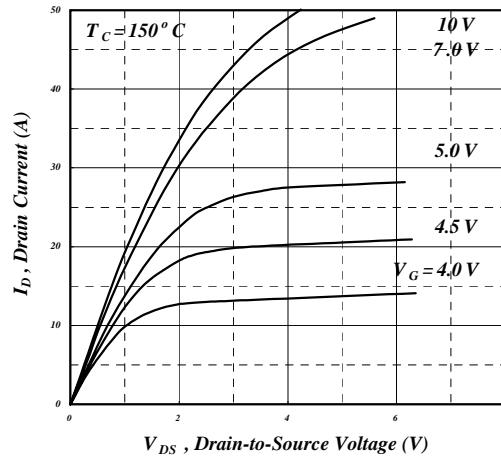


Fig 2. Typical Output Characteristics

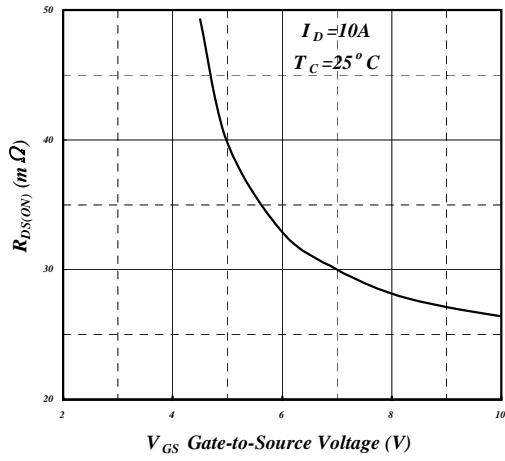


Fig 3. On-Resistance v.s. Gate Voltage

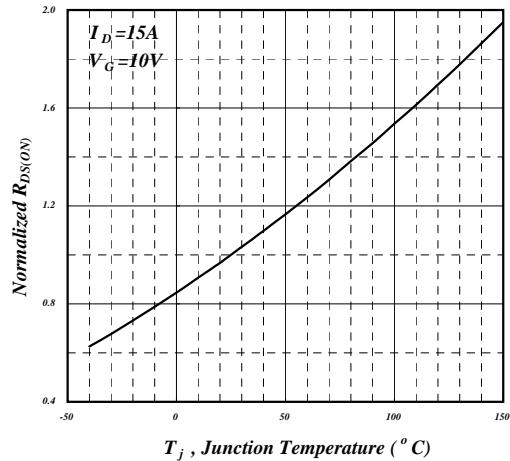


Fig 4. Normalized On-Resistance v.s. Junction Temperature

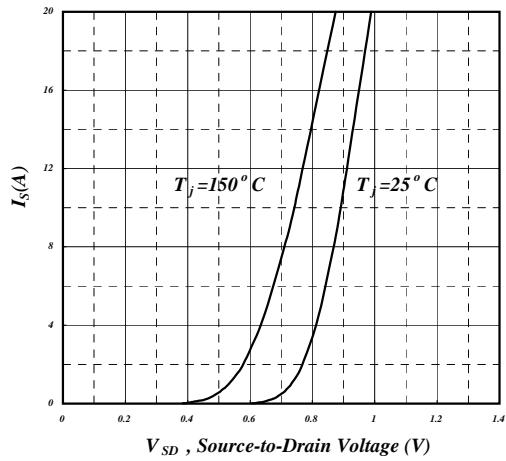


Fig 5. Forward Characteristic of Reverse Diode

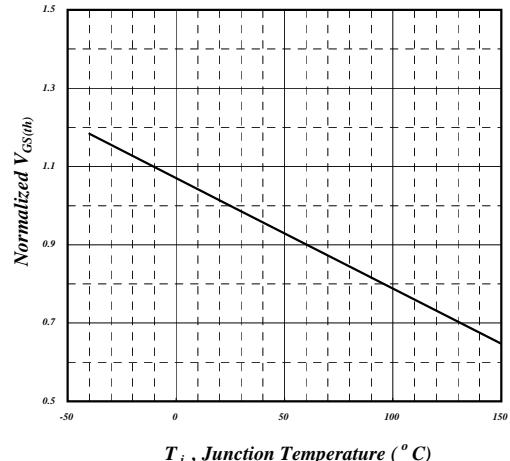
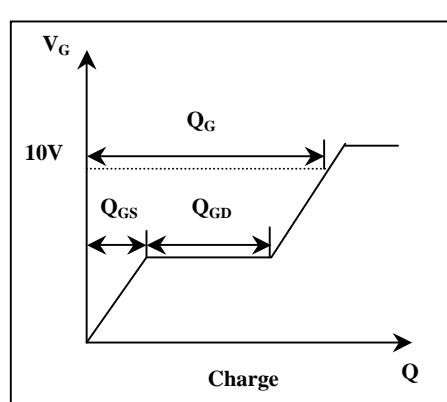
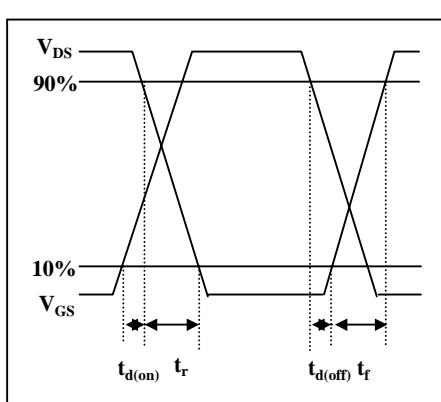
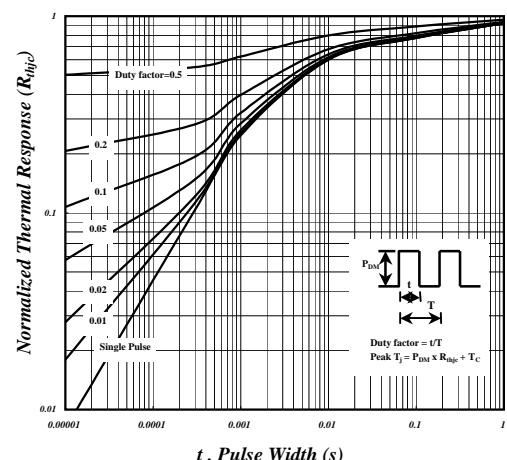
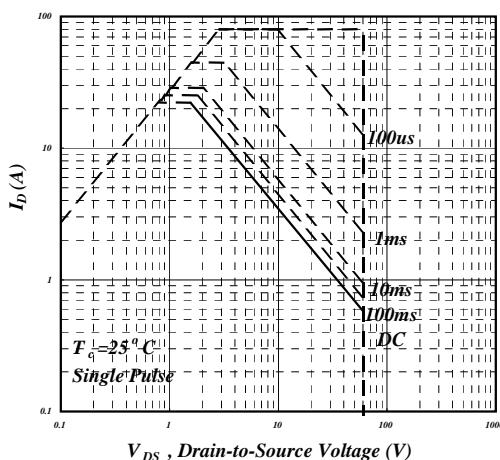
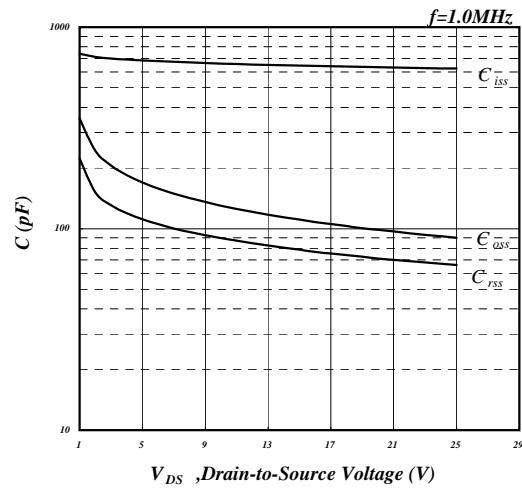
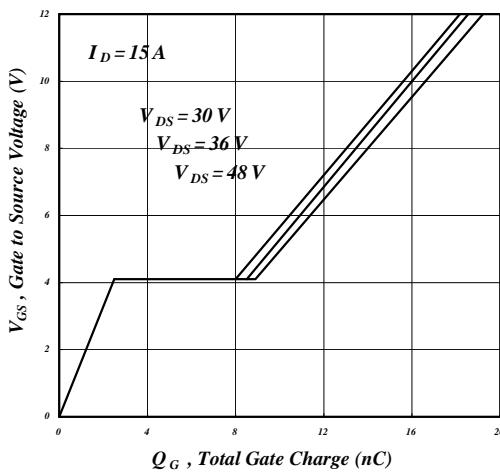


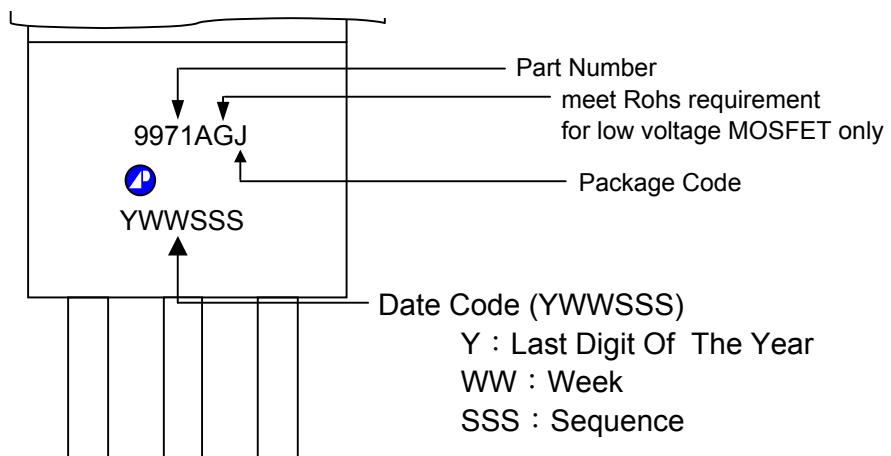
Fig 6. Gate Threshold Voltage v.s. Junction Temperature





MARKING INFORMATION

TO-251



TO-252

